

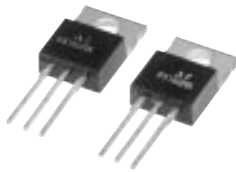
**PRELIMINARY**  
 Notice: This is not a final specification.  
 Some parametric limits are subject to change.

MITSUBISHI Nch POWER MOSFET

# FS16UMA-5A

HIGH-SPEED SWITCHING USE

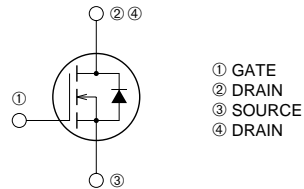
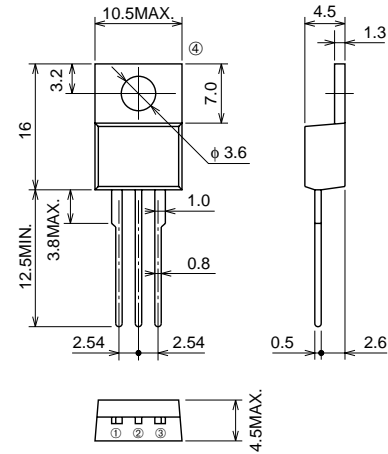
## FS16UMA-5A



- 10V DRIVE
- $V_{DSS}$  ..... 250V
- $r_{DS(ON)}$  (MAX) ..... 0.25 $\Omega$
- $I_D$  ..... 16A

## OUTLINE DRAWING

Dimensions in mm



TO-220

## APPLICATION

Cs Switch for CRT Display monitor

## MAXIMUM RATINGS ( $T_c = 25^\circ\text{C}$ )

Symbol	Parameter	Conditions	Ratings	Unit
$V_{DSS}$	Drain-source voltage	$V_{GS} = 0V$	250	V
$V_{GSS}$	Gate-source voltage	$V_{DS} = 0V$	$\pm 20$	V
$I_D$	Drain current		16	A
$I_{DM}$	Drain current (Pulsed)		48	A
$I_{DA}$	Avalanche drain current (Pulsed)	$L = 200\mu\text{H}$	16	A
PD	Maximum power dissipation		80	W
$T_{ch}$	Channel temperature		$-55 \sim +150$	$^\circ\text{C}$
$T_{stg}$	Storage temperature		$-55 \sim +150$	$^\circ\text{C}$
—	Weight	Typical value	2.0	g

Sep.1998



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**ELECTRICAL CHARACTERISTICS** ( $T_{ch} = 25^{\circ}\text{C}$ )

Symbol	Parameter	Test conditions	Limits			Unit
			Min.	Typ.	Max.	
V (BR) DSS	Drain-source breakdown voltage	$I_D = 1\text{mA}, V_{GS} = 0\text{V}$	250	—	—	V
I <sub>GSS</sub>	Gate-source leakage current	$V_{GS} = \pm 20\text{V}, V_{DS} = 0\text{V}$	—	—	$\pm 10$	$\mu\text{A}$
I <sub>DSS</sub>	Drain-source leakage current	$V_{DS} = 250\text{V}, V_{GS} = 0\text{V}$	—	—	1	mA
V <sub>GS</sub> (th)	Gate-source threshold voltage	$I_D = 1\text{mA}, V_{DS} = 10\text{V}$	2.0	3.0	4.0	V
r <sub>DS</sub> (ON)	Drain-source on-state resistance	$I_D = 8\text{A}, V_{GS} = 10\text{V}$	—	0.19	0.25	$\Omega$
V <sub>DS</sub> (ON)	Drain-source on-state voltage	$I_D = 8\text{A}, V_{GS} = 10\text{V}$	—	1.52	2.00	V
y <sub>fs</sub>	Forward transfer admittance	$I_D = 8\text{A}, V_{DS} = 10\text{V}$	—	16.0	—	S
C <sub>iss</sub>	Input capacitance	$V_{DS} = 25\text{V}, V_{GS} = 0\text{V}, f = 1\text{MHz}$	—	1850	—	pF
C <sub>oss</sub>	Output capacitance		—	180	—	pF
C <sub>rss</sub>	Reverse transfer capacitance		—	50	—	pF
t <sub>d</sub> (on)	Turn-on delay time	$V_{DD} = 150\text{V}, I_D = 8\text{A}, V_{GS} = 10\text{V}, R_{GEN} = R_{GS} = 50\Omega$	—	30	—	ns
t <sub>r</sub>	Rise time		—	50	—	ns
t <sub>d</sub> (off)	Turn-off delay time		—	320	—	ns
t <sub>f</sub>	Fall time		—	70	—	ns
V <sub>SD</sub>	Source-drain voltage	$I_S = 8\text{A}, V_{GS} = 0\text{V}$	—	0.95	—	V
R <sub>th</sub> (ch-c)	Thermal resistance	Channel to case	—	—	1.56	$^{\circ}\text{C/W}$